

Conf. Ag

4 a second substrate with a metal film formed thereon, said
5 second substrate bonded with the metal film to said semiconductor
6 film of said first substrate.--

1 --15. The apparatus of claim 14 wherein said semiconductor
2 film demarcated from a rest of said first substrate by a damaged
3 surface.--

1 --16. The apparatus of claim 15 wherein said damaged surface
2 formed by ion implantation.--

Sub C2
17. The apparatus of claim 14 wherein said metal includes a
noble metal.--

1 --18. The apparatus of claim 14 wherein said first
2 semiconductor film has a first oxide film formed thereon.--

Sub C3
19. The apparatus of claim 14 wherein said metal film is
formed on a second film of oxide formed on said second substrate.--

Sub B2
1 --20. An apparatus comprising:
2 a substrate;
3 a first oxide film formed on said substrate;
4 a metal film formed on said first oxide film;
5 a second oxide layer formed on said metal film; and
6 a semiconductor film formed on said second oxide film, said
7 semiconductor film having a least one active device formed
8 therein.--

21. The apparatus of claim 20 wherein said metal film includes
a noble metal.--